

April 2006

FOD0708 Single Channel CMOS Optocoupler

FOD0738 Dual Channel CMOS Optocoupler

Features

- +5 V CMOS compatibility
- 15 ns typical pulse width distortion
- 30 ns max. pulse width distortion
- 40 ns max. propagation delay skew
- High speed: 15 MBd
- 60 ns max. propagation delay
- 10 kV/μs minimum common mode rejection
- -40°C to 100°C temperature range
- UL approved (file #E90700)

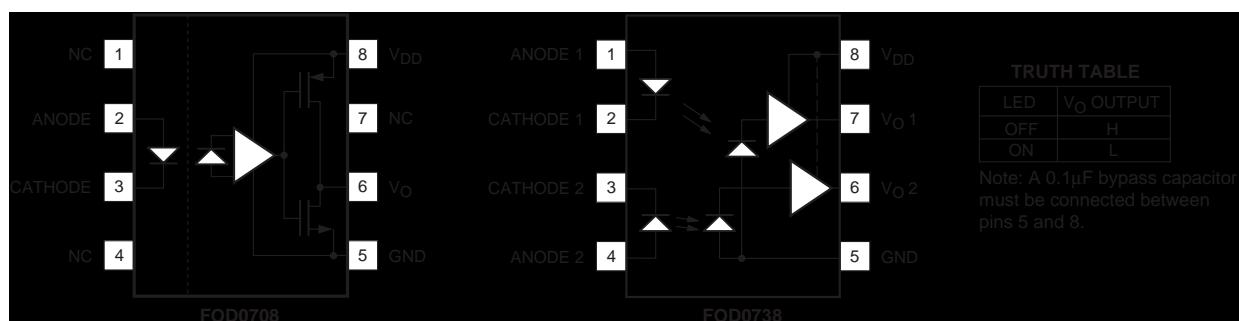
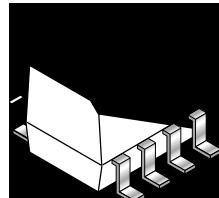
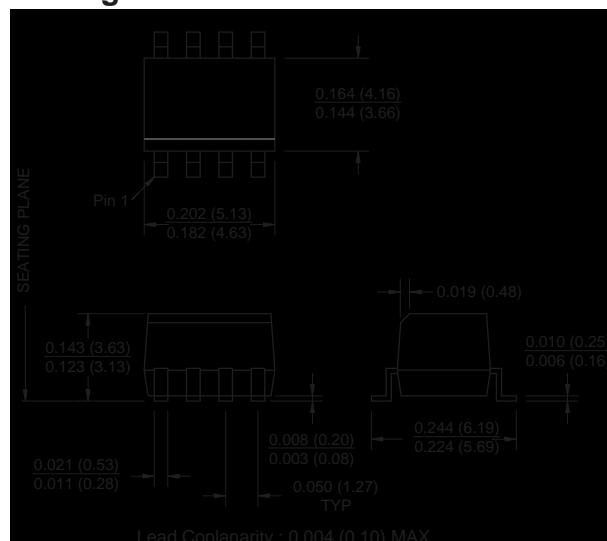
Applications

- Line receivers
- Pulse transformer replacement
- Output interface to CMOS-LSTTL-TTL
- Wide bandwidth analog coupling

General Description

The FOD0708 and FOD0738 optocouplers consist of an AlGaAs LED optically coupled to a high speed trans-impedance amplifier and voltage comparator. These optocouplers utilize the latest CMOS IC technology to achieve outstanding performance with very low power consumption. The devices are housed in a compact 8-pin SOIC package for optimum mounting density.

Package Dimensions



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Max.	Units
T_S	Storage Temperature	-40	+125	°C
T_A	Ambient Operating Temperature	-40	+100	°C
V_{DD}	Supply Voltages	0	6	Volts
V_O	Output Voltage	-0.5	$V_{DD} + 0.5$	Volts
I_O	Average Output Current		2	mA
I_F	Average Forward Input Current		20	mA
	Lead Solder Temperature	260°C for 10 sec., 1.6 mm below seating plane		
	Solder Reflow Temperature Profile	See Solder Reflow Temperature Profile Section		
	LED Power Dissipation Single Channel Dual Channel	40 mW (derate above 95°C, 1.4 mW/°C) 40 mW per channel (derate above 90°C, 1.2 mW/°C)		
	Detector Power Dissipation Single Channel Dual Channel	85 mW (derate above 75°C, 1.8 mW/°C) 65 mW per channel (derate above 90°C, 2.0 mW/°C)		

Recommended Operating Conditions

Symbol	Parameter	Min.	Max.	Units
T_A	Ambient Operating Temperature	-40	+100	°C
V_{DD}	Supply Voltages	4.5	5.5	Volts
I_F	Input Current (ON)	10	16	mA

Electrical Characteristics ($T_A = -40^\circ\text{C}$ to $+100^\circ\text{C}$) and $4.5 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$

Symbol	Parameter	Test Conditions	Min.	Typ.*	Max.	Units	Fig.
V_F	Input Forward Voltage	$I_F = 12 \text{ mA}$	1.3	1.45	1.8	V	9
BV_R	Input Reverse Breakdown Voltage	$I_R = 10 \mu\text{A}$	5			V	
V_{OH}	Logic High Output Voltage	$I_F = 0, I_O = -20 \mu\text{A}$	4.0	5.0		V	
V_{OL}	Logic Low Output Voltage	$I_F = 12 \text{ mA}, I_O = 20 \mu\text{A}$		0.01	0.1	V	
I_{TH}	Input Threshold Current (FOD0708) (FOD0738)	$I_{OL} = 20 \mu\text{A}$		4.0 4.4	8.2 8.2	mA	1,5
I_{DDL}	Logic Low Output Supply Current (FOD0708) (FOD0738)	$I_F = 12 \text{ mA}$		3.4 6.9	14.0 18.0	mA	3,7
I_{DDH}	Logic High Output Supply Current (FOD0708) (FOD0738)	$I_F = 0$		3.7 7.5	11.0 15.0	mA	4,8

*All typicals at $T_A = 25^\circ\text{C}$ and $V_{DD} = 5\text{V}$ unless otherwise noted.

Switching Characteristics Over recommended temperature ($T_A = -40^\circ\text{C}$ to $+100^\circ\text{C}$) and $4.5 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$. All typical specifications are at $T_A = 25^\circ\text{C}$, $V_{DD} = +5 \text{ V}$.

Symbol	Parameter	Test Conditions		Min.	Typ.*	Max.	Units
t_{PHL}	Propagation Delay Time to Logic Low Output	$I_F = 12 \text{ mA}$, $C_L = 15 \text{ pF}$ CMOS Signal Levels, note 1, fig. 10		20		60	ns
t_{PLH}	Propagation Delay Time to Logic High Output	$I_F = 12 \text{ mA}$, $C_L = 15 \text{ pF}$ CMOS Signal Levels, note 1, fig. 10	FOD0708	13		60	ns
			FOD0738	11		60	
PW	Pulse Width			100			ns
$ PWD $	Pulse Width Distortion	$I_F = 12 \text{ mA}$, $C_L = 15 \text{ pF}$ CMOS Signal Levels, note 2		0		30	ns
t_{PSK}	Propagation Delay Skew	$I_F = 12 \text{ mA}$, $C_L = 15 \text{ pF}$ CMOS Signal Levels, note 3				40	ns
t_R	Output Rise Time (10%–90%)	$I_F = 12 \text{ mA}$, $C_L = 15 \text{ pF}$ CMOS Signal Levels			12		ns
t_F	Output Fall Time (90%–10%)	$I_F = 12 \text{ mA}$, $C_L = 15 \text{ pF}$ CMOS Signal Levels			8		ns
$ CM_H $	Common Mode Transient Immunity at Logic High Output	$V_{CM} = 1000 \text{ V}$, $T_A = 25^\circ\text{C}$, $I_F = 0 \text{ mA}$, note 4, fig. 11		25	50		kV/ μs
$ CM_L $	Common Mode Transient Immunity at Logic Low Output	$V_{CM} = 1000 \text{ V}$, $T_A = 25^\circ\text{C}$, $I_F = 12 \text{ mA}$, note 5, fig. 11		25	50		kV/ μs

*All typicals at $T_A = 25^\circ\text{C}$ and $V_{DD} = 5\text{V}$ unless otherwise noted.

Isolation Characteristics ($T_A = -40^\circ\text{C}$ to $+100^\circ\text{C}$ Unless otherwise specified.)

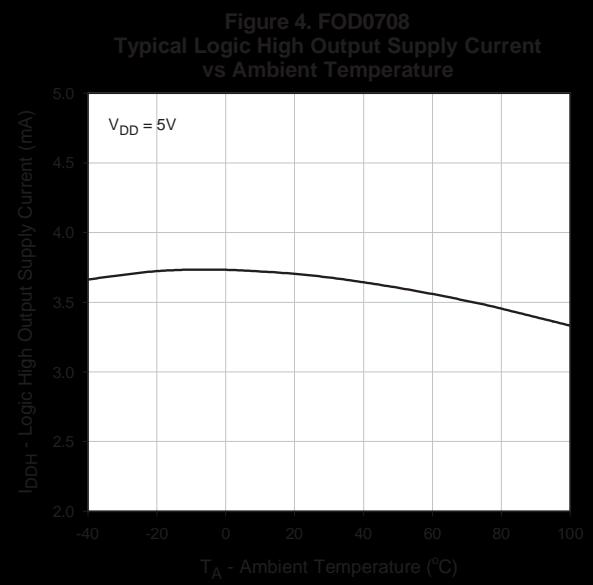
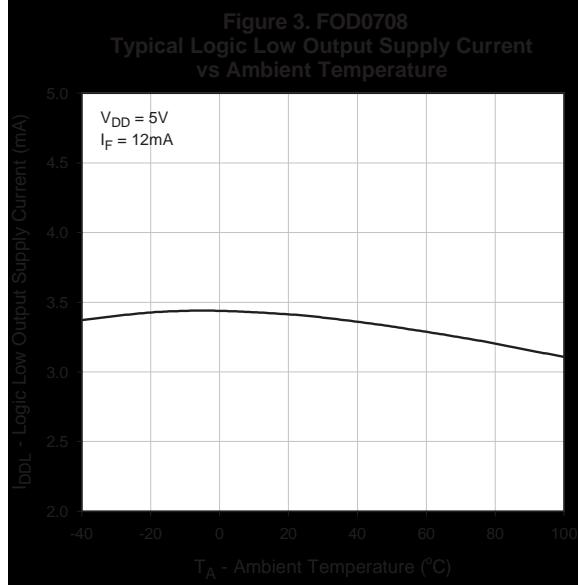
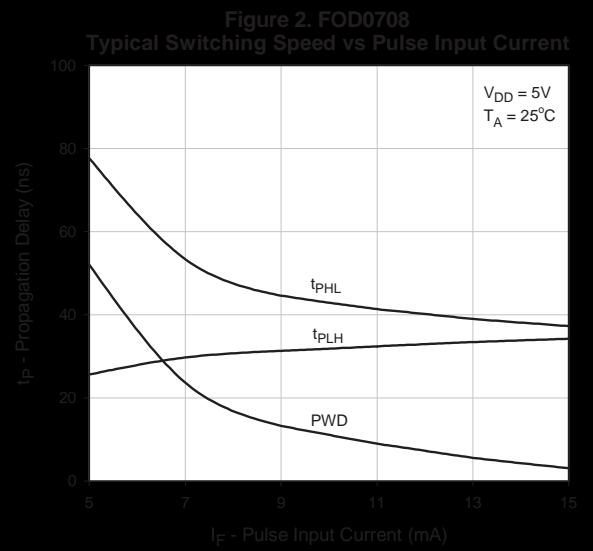
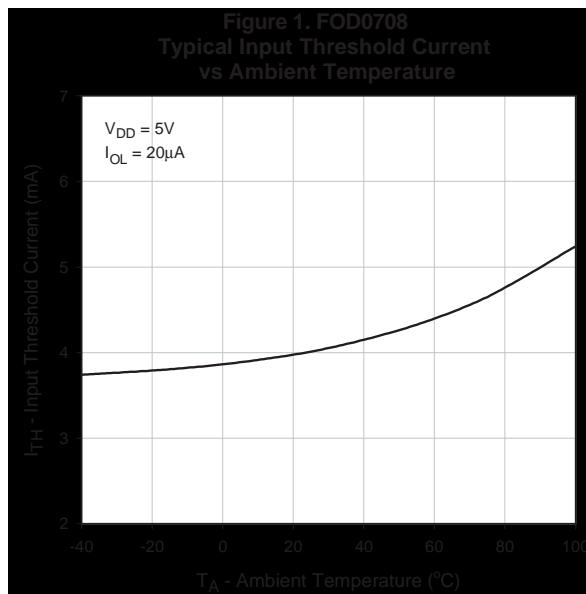
Characteristics	Test Conditions	Symbol	Min	Typ.**	Max	Unit
Input-Output Insulation Leakage Current	(Relative humidity = 45%) ($T_A = 25^\circ\text{C}$, $t = 5 \text{ s}$) ($V_{I-O} = 3000 \text{ VDC}$) (Note 6)	I_{I-O}			1.0	μA
Withstand Insulation Test Voltage	($I_{I-O} \leq 10 \mu\text{A}$, $R_H < 50\%$, $T_A = 25^\circ\text{C}$) ($t = 1 \text{ min.}$) (Note 6)	V_{ISO}	2500			V_{RMS}
Resistance (Input to Output)	($V_{I-O} = 500 \text{ V}$) (Note 6)	R_{I-O}		10^{12}		Ω
Capacitance (Input to Output)	($f = 1 \text{ MHz}$) (Note 6)	C_{I-O}		0.6		pF

** All typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^\circ\text{C}$

Notes:

1. Propagation delay time, high to low (t_{PHL}), is measured from the 50% level on the rising edge of the input pulse to the 2.5V level of the falling edge of the output voltage signal. Propagation delay time, low to high (t_{PLH}), is measured from the 50% level on the falling edge of the input pulse to the 2.5V level of the rising edge of the output voltage signal.
2. Pulse width distortion is defined as the absolute difference between the high to low and low to high propagation delay times, $|t_{PHL} - t_{PLH}|$.
3. Propagation delay skew, t_{PSK} , is defined as the worst case difference in t_{PHL} or t_{PLH} between units within the recommended operating range of the device.
4. CM_H – The maximum tolerated rate of rise of the common mode voltage to ensure the output will remain in the high state, (i.e., $V_{OUT} > 2.0\text{V}$) Measured in kilovolts per microsecond (kV/ μs).
5. CM_L – The maximum tolerated rate of fall of the common mode voltage to ensure the output will remain in the low state, (i.e., $V_{OUT} < 0.8\text{V}$). Measured in kilovolts per microsecond (kV/ μs).
6. Isolation voltage, V_{ISO} , is an internal device dielectric breakdown rating. For this test, pins 1,2,3,4 are common, and pins 5,6,7,8 are common.

Typical Characteristics



Typical Characteristics (Continued)

Figure 5. FOD0738
Typical Input Threshold Current
vs Ambient Temperature

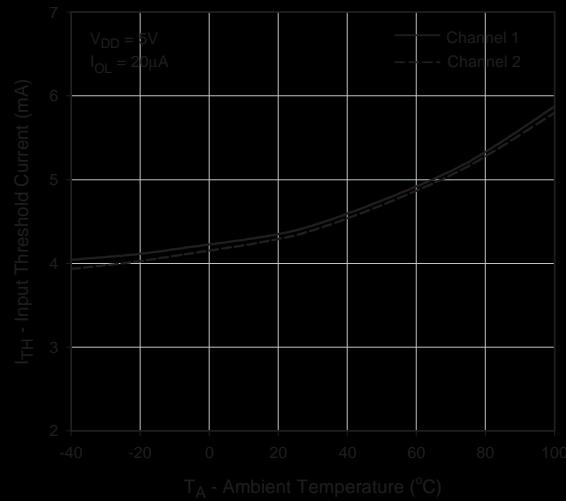


Figure 6. FOD0738
Typical Switching Speed vs Pulse Input Current

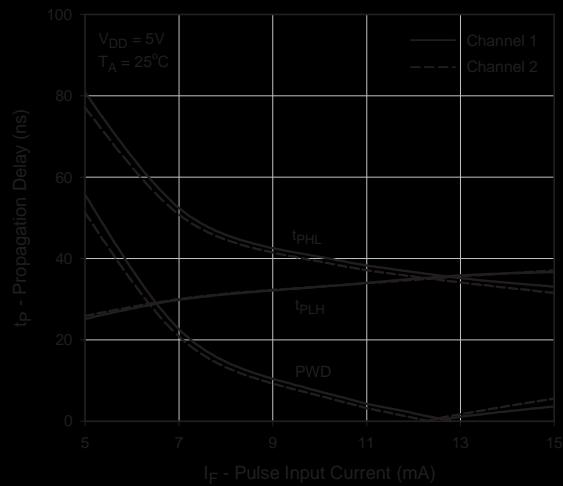


Figure 7. FOD0738
Typical Logic Low Output Supply Current
vs Ambient Temperature

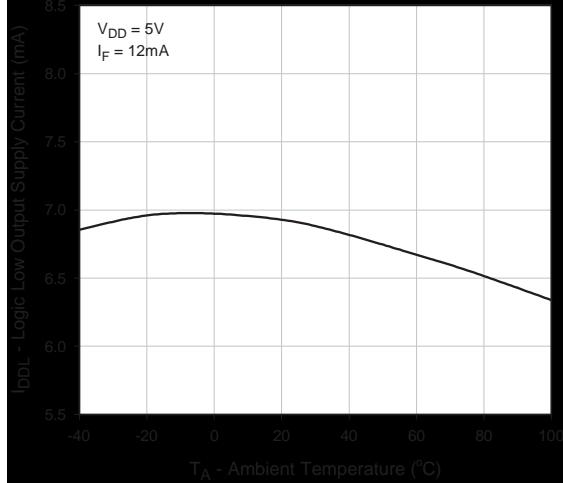
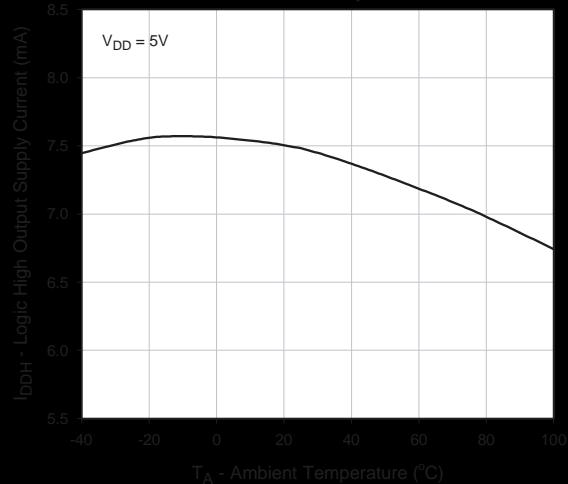
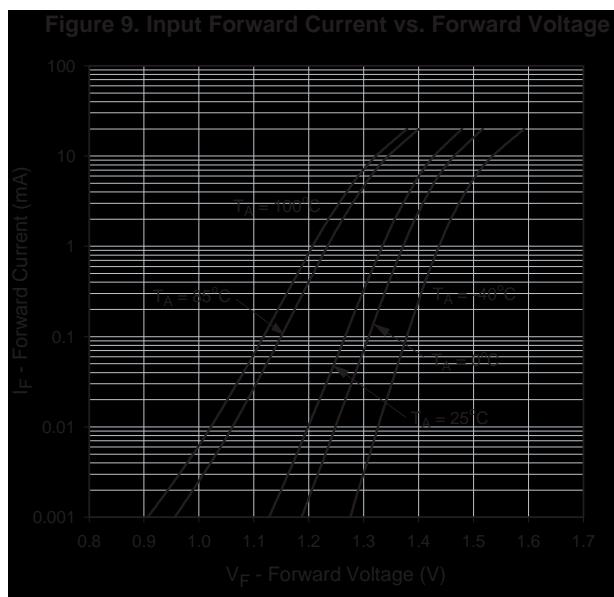


Figure 8. FOD0738
Typical Logic High Output Supply Current
vs Ambient Temperature



Typical Characteristics (Continued)



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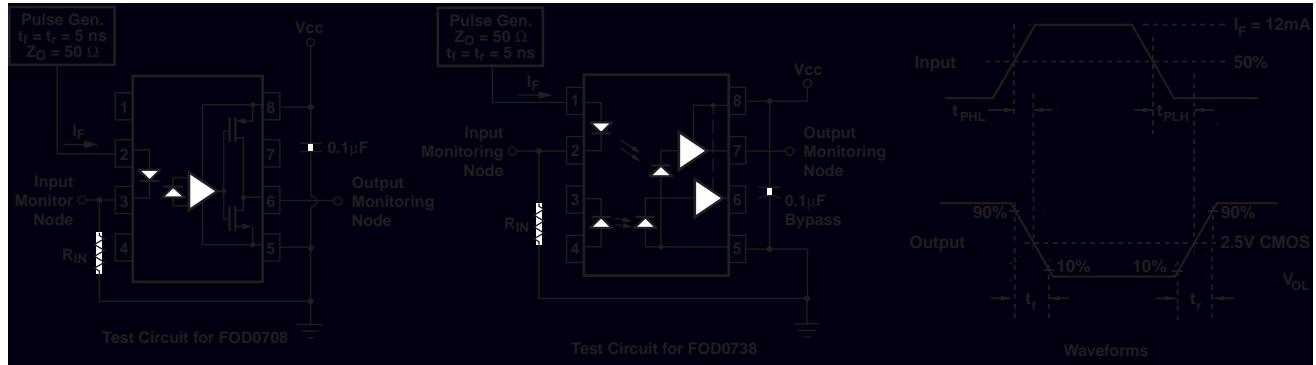


Fig. 10 Test Circuit and Waveforms for t_{PLH} , t_{PHL} , t_f and t_r .

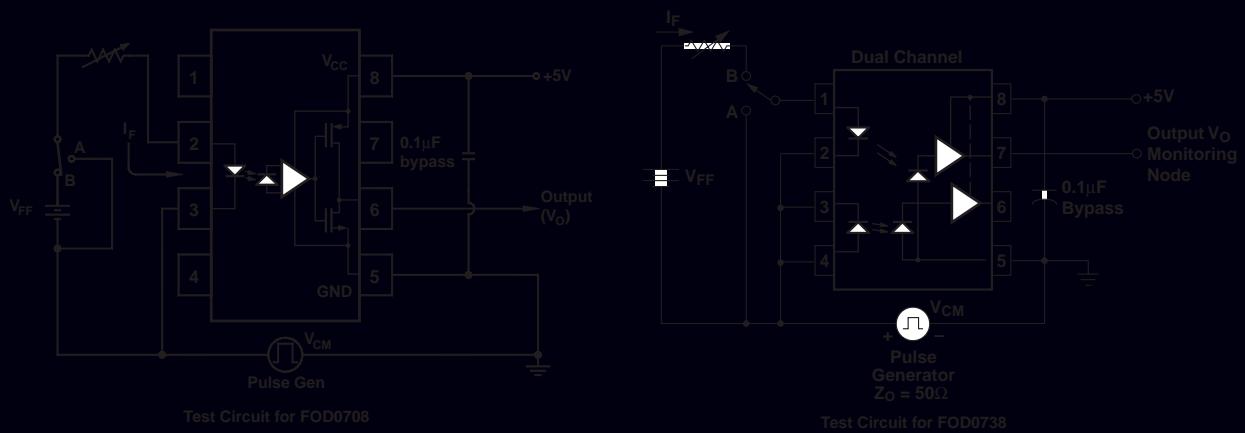
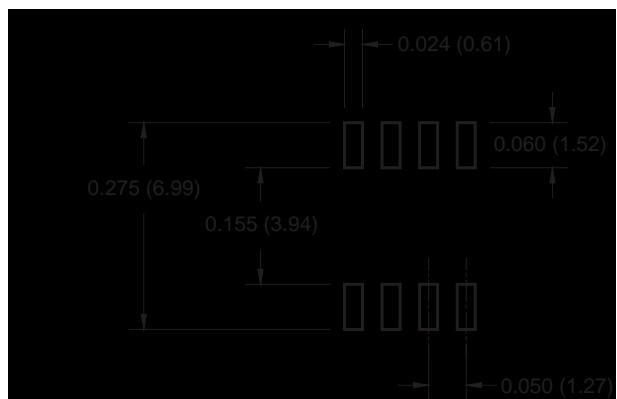


Fig. 11 Test Circuit Common Mode Transient Immunity (FOD0708 and FOD0738)

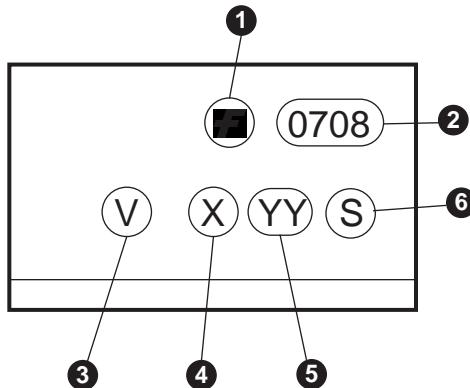
8-Pin Small Outline



Ordering Information

Option	Order Entry Identifier	Description
No Suffix	FOD0708	Shipped in tubes (50 units per tube)
R1	FOD0708R1	Tape and Reel (500 units per reel)
R2	FOD0708R2	Tape and Reel (2500 units per reel)

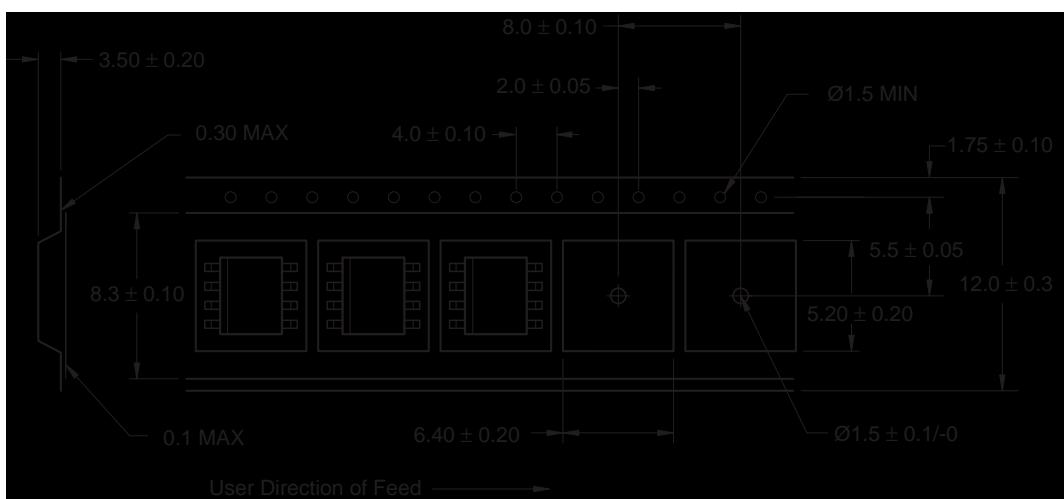
Marking Information



Definitions

1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '5'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

Carrier Tape Specification



Reflow Profile

